

| | Document ID | Pages | Title | Current OR | Current XRef | Inventor |
|---|---------------|-------|--|------------|---|-----------------------------|
| 1 | US 6074917 A | 8 | LPCVD oxide and RTA for top oxide of ONO film to improve reliability for flash memory devices | 438/261 | 257/E29.129; 257/E29.165; 438/786; 438/954 | Chang, Kent Kuohua et al. |
| 2 | US 6376341 B1 | 8 | Optimization of thermal cycle for the formation of pocket implants | 438/510 | 438/257; 438/258; 438/266 | Kluth, George J. et al. |
| 3 | US 6306777 B1 | 9 | Flash memory having a treatment layer disposed between an interpoly dielectric structure and method of forming | 438/763 | 257/639; 257/640; 257/646; 257/649; 438/758; 438/761; 438/787; 438/791 | Ogle, Jr., Robert B. et al. |